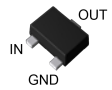
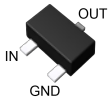
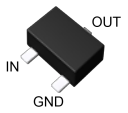
DTC024X series

NPN 100mA 50V Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

Parameter	Value
V_{CC}	50V
$I_{C(MAX.)}$	100mA
R_1	22kΩ
R_2	47kΩ

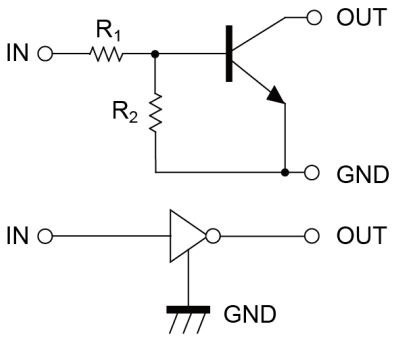
●Outline

VMT3  DTC024XM (SC-105AA)	EMT3F  DTC024XEB (SC-89)
UMT3F  DTC024XUB (SC-85)	

●Features

1) Built-In Biasing Resistors, R_1 = 22kΩ, R_2 = 47kΩ
2) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit) .
3) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
4) Only the on/off conditions need to be set for operation, making the circuit design easy.
5) Complementary PNP Types: DTA024X series
6) Lead Free/RoHS Compliant.

●Inner circuit



●Application

Switching circuit, Inverter circuit, Interface circuit, Driver circuit

●Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
DTC024XM	VMT3	1212	T2L	180	8	8000	69
DTC024XEB	EMT3F	1616	TL	180	8	3000	69
DTC024XUB	UMT3F	2021	TL	180	8	3000	69

●Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Values	Unit
Supply voltage		V_{CC}	50	V
Input voltage		V_{IN}	40 to -7	V
Output current		I_O	50	mA
Collector current		$I_{C(MAX)}$*1	100	mA
Power dissipation	DTC024XM	P_D*2	150	mW
	DTC024XEB		150	
	DTC024XUB		200	
Junction temperature		T_j	150	℃
Range of storage temperature		T_{stg}	-55 to +150	℃

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input voltage	$V_{I(off)}$	V_{CC} = 5V, I_O = 100μA	-	-	0.5	V
	$V_{I(on)}$	V_O = 0.3V, I_O = 5mA	2.5	-	-	
Output voltage	$V_{O(on)}$	I_O / I_I = 5mA / 0.5mA	-	0.05	0.15	V
Input current	I_I	V_I = 5V	-	-	0.36	mA
Output current	$I_{O(off)}$	V_{CC} = 50V, V_I = 0V	-	-	500	nA
DC current gain	G_I	V_O = 10V, I_O = 5mA	80	-	-	-
Input resistance	R_1	-	15.4	22	28.6	kΩ
Resistance ratio	R_2/R_1	-	1.7	2.1	2.6	-
Transition frequency	f_T*1	V_{CE} = 10V, I_E = -5mA, f = 100MHz	-	250	-	MHz

*1 Characteristics of built-in transistor

*2 Each terminal mounted on a reference footprint

●Electrical characteristic curves (T_a =25°C)

Fig.1 Input voltage vs. output current (ON characteristics)

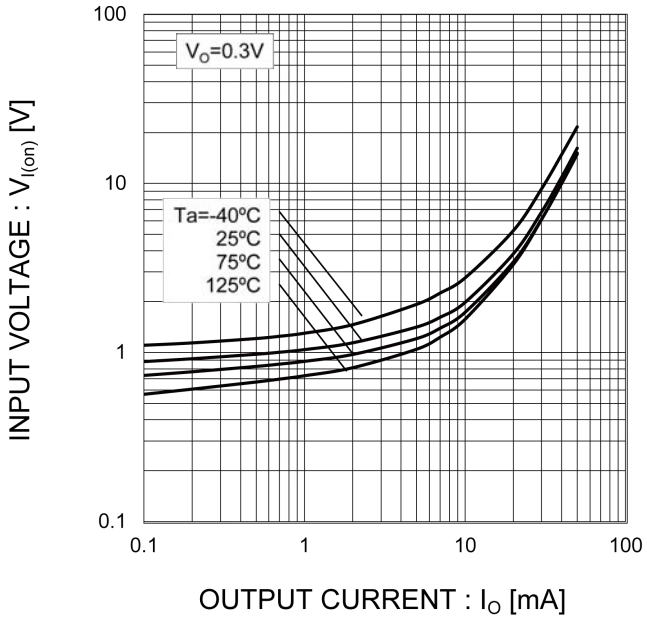


Fig.2 Output current vs. input voltage (OFF characteristics)

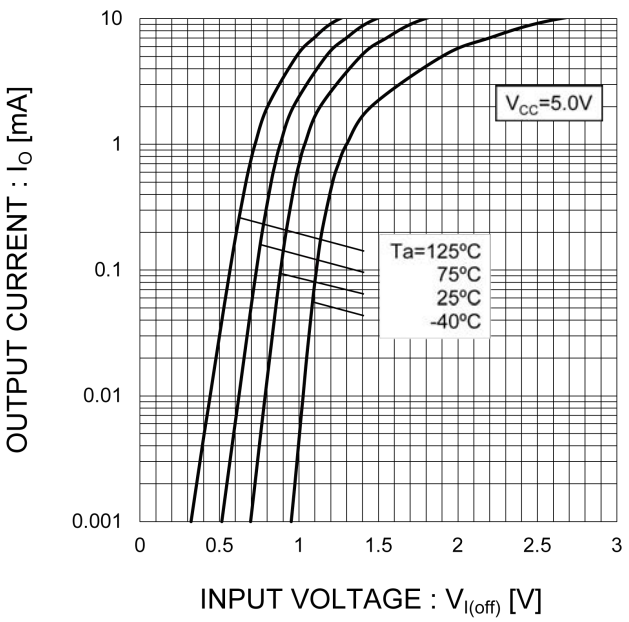


Fig.3 Output current vs. output voltage

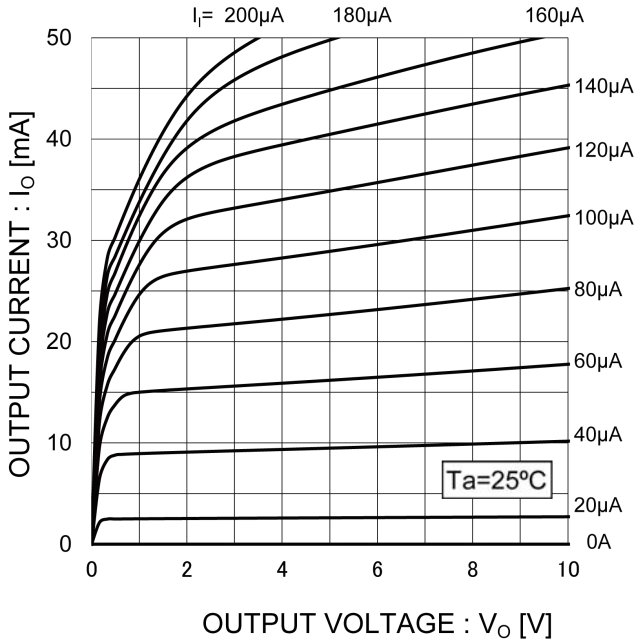
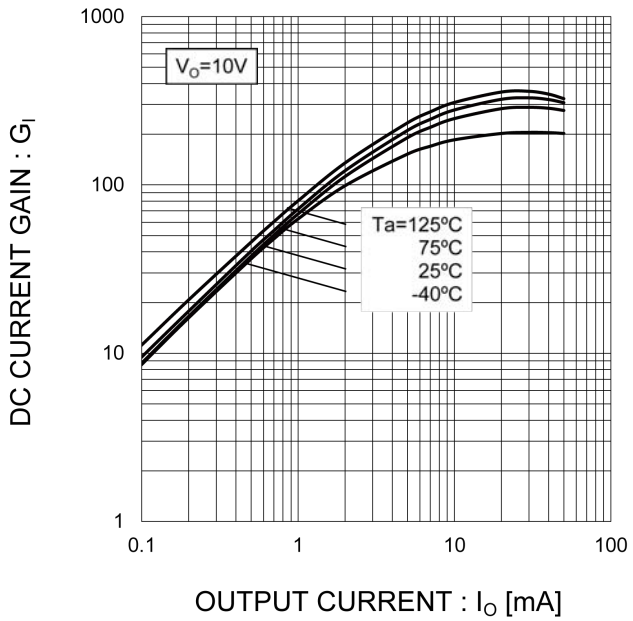
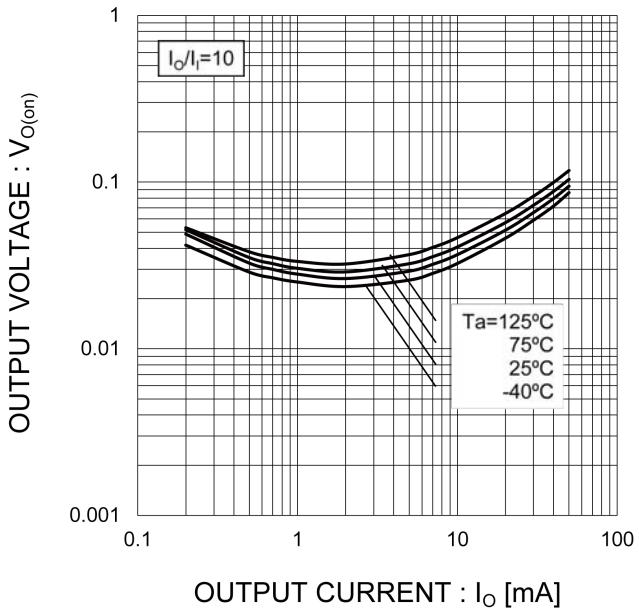


Fig.4 DC current gain vs. output current



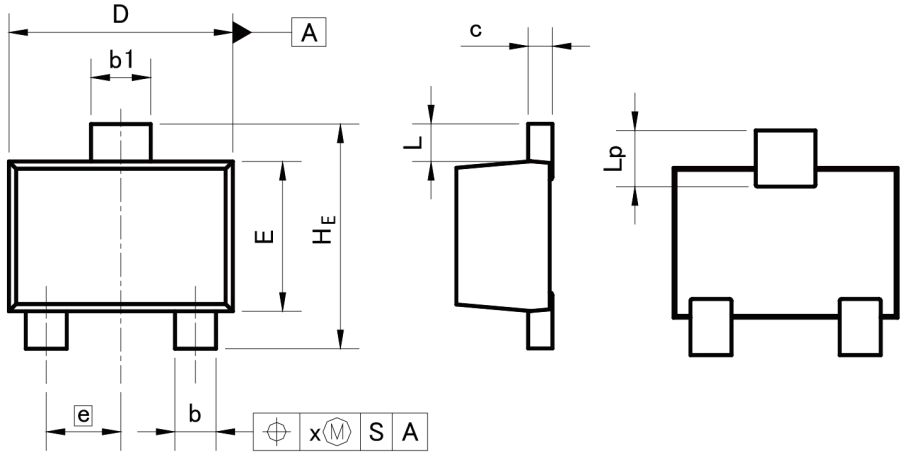
●Electrical characteristic curves (T_a =25°C)

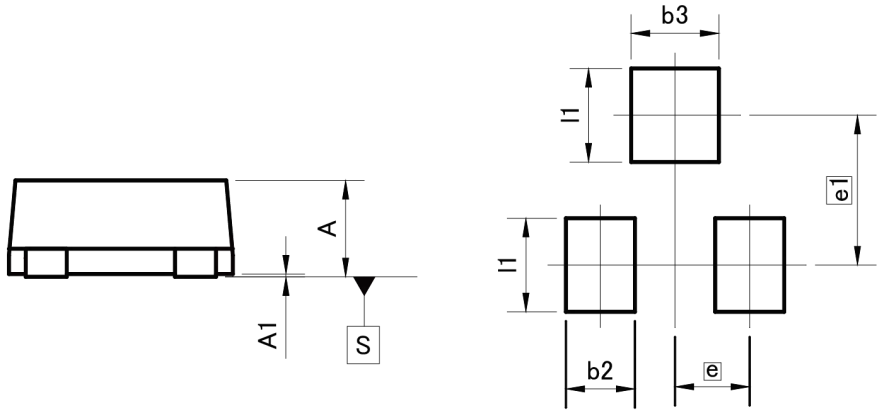
Fig.5 Output voltage vs. output current



●Dimensions

VMT3





Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

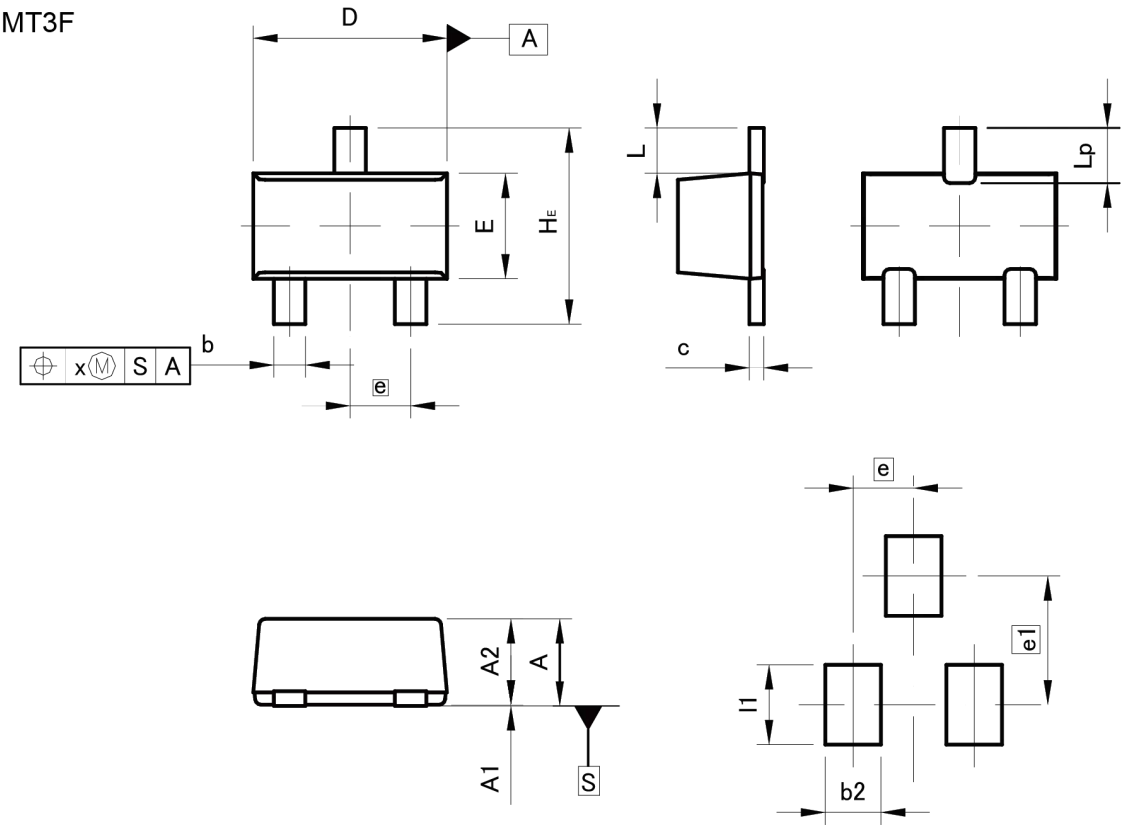
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.45	0.55	0.018	0.022
A1	0.00	0.10	0.000	0.004
b	0.17	0.27	0.007	0.011
b1	0.27	0.37	0.011	0.015
c	0.08	0.18	0.003	0.007
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
e	0.40		0.02	
HE	1.10	1.30	0.043	0.051
L	0.10	0.30	0.004	0.012
Lp	0.20	0.40	0.008	0.016
x	−	0.10	−	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	−	0.37	−	0.015
b3	−	0.47	−	0.019
e1	0.80		0.031	
l1	−	0.50	−	0.020

Dimension in mm/inches

●Dimensions

EMT3F



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

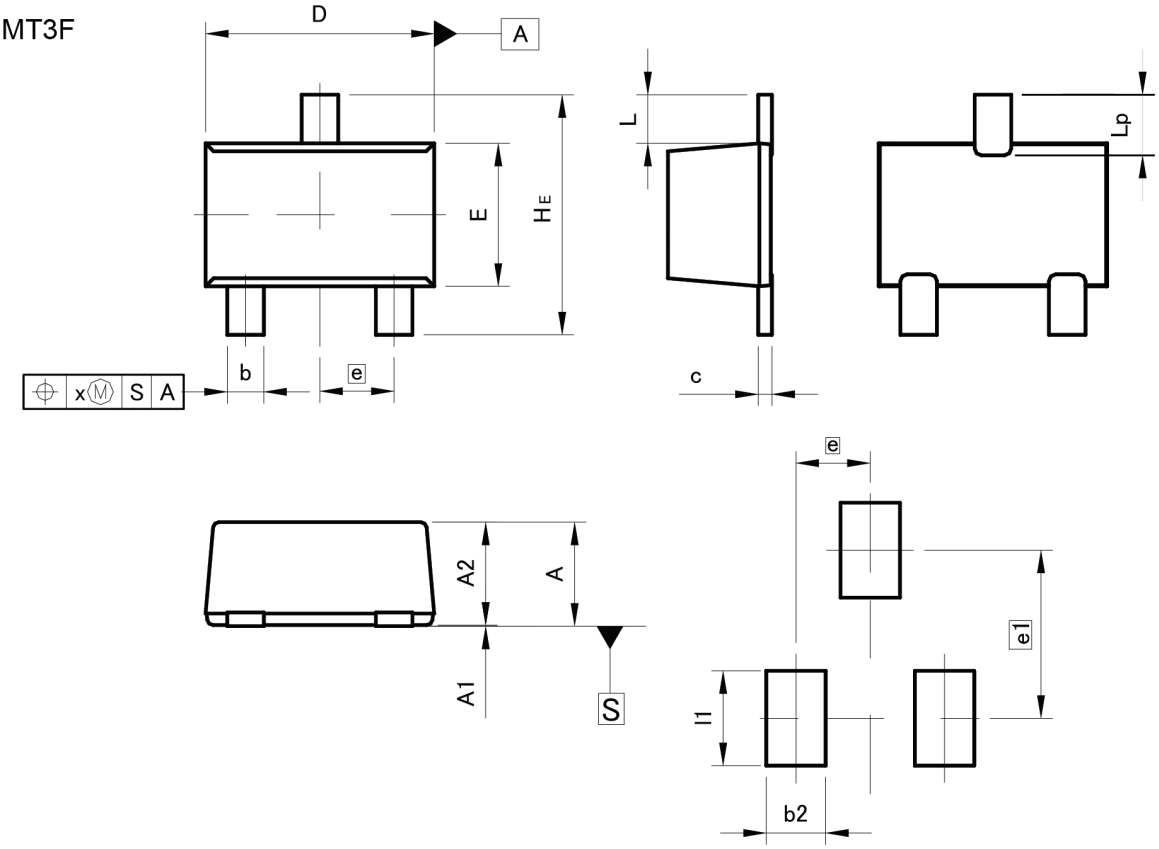
DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.65	0.85	0.026	0.033
A1	0.00	0.10	0.000	0.004
A2	0.60	0.80	0.024	0.031
b	0.21	0.36	0.008	0.014
c	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	0.76	0.96	0.030	0.038
e	0.50		0.020	
HE	1.50	1.70	0.059	0.067
L	0.37		0.015	
Lp	0.35	0.55	0.014	0.022
x	–	0.10	–	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	–	0.46	–	0.018
e1	–	1.05	–	0.041
l1	–	0.65	–	0.026

Dimension in mm/inches

●Dimensions

UMT3F



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.85	1.05	0.033	0.041
A1	0.00	0.10	0.000	0.004
A2	0.80	1.00	0.031	0.039
b	0.27	0.42	0.011	0.017
c	0.08	0.18	0.003	0.007
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
e	0.65		0.026	
HE	2.00	2.20	0.079	0.087
L	0.43		0.017	
Lp	0.43	0.63	0.017	0.025
x	–	0.10	–	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	–	0.52	–	0.020
e1	1.47		0.058	
l1	–	0.83	–	0.033

Dimension in mm/inches

Notes

1) The information contained herein is subject to change without notice.

2) Before you use our Products, please contact our sales representative and verify the latest specifications :

3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.
Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.

4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.

6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.

7) The Products specified in this document are not designed to be radiation tolerant.

8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.

9) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.

10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.

11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.

12) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.

13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.

14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.

ROHM SEMICONDUCTOR

Thank you for your accessing to ROHM product informations.
More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/